

FQAF11N90C

900V N-Channel MOSFET

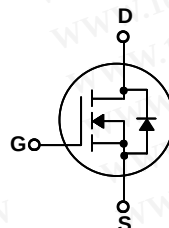
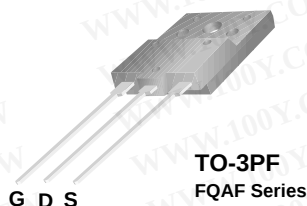
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies..

Features

- 7.0A, 900V, $R_{DS(on)} = 1.1\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 60 nC)
- Low C_{rss} (typical 23 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQAF11N90C	Units
V_{DSS}	Drain-Source Voltage	900	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	7.0	A
	- Continuous ($T_C = 100^\circ\text{C}$)	4.4	A
I_{DM}	Drain Current - Pulsed (Note 1)	28.0	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	960	mJ
I_{AR}	Avalanche Current (Note 1)	7.0	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	120	W
	- Derate above 25°C	0.96	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.04	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

Electrical Characteristics

 $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	900	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	1.0	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 900\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 720\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3.5\text{ A}$	--	0.91	1.1	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 3.5\text{ A}$ (Note 4)	--	--	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2530	3290	pF
C_{oss}	Output Capacitance		--	215	280	pF
C_{rss}	Reverse Transfer Capacitance		--	23	30	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 450\text{ V}, I_D = 11.0\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	60	130	ns
t_r	Turn-On Rise Time		--	130	270	ns
$t_{d(off)}$	Turn-Off Delay Time		--	130	270	ns
t_f	Turn-Off Fall Time		--	85	180	ns
Q_g	Total Gate Charge	$V_{DS} = 720\text{ V}, I_D = 11.0\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	60	80	nC
Q_{gs}	Gate-Source Charge		--	13	--	nC
Q_{gd}	Gate-Drain Charge		--	25	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	7.0	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	28.0	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 7.0 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 11.0 A,	--	1000	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs (Note 4)	--	17.0	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 37\text{ mH}, I_{AS} = 7.0\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 11.0\text{ A}, dI/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

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Typical Characteristics

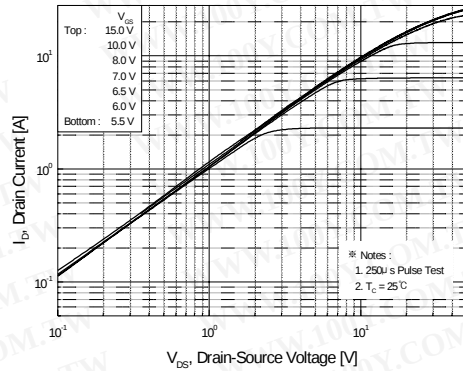


Figure 1. On-Region Characteristics

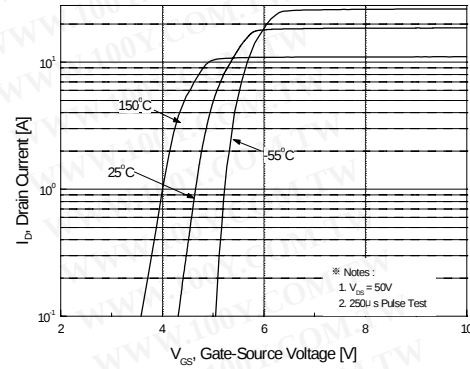


Figure 2. Transfer Characteristics

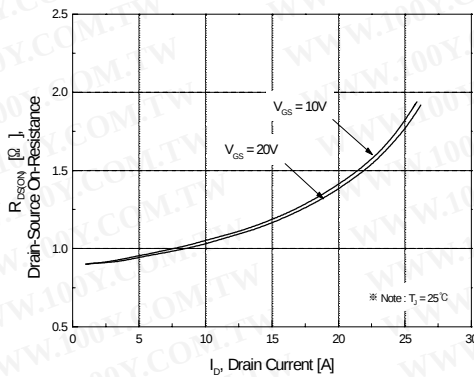


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

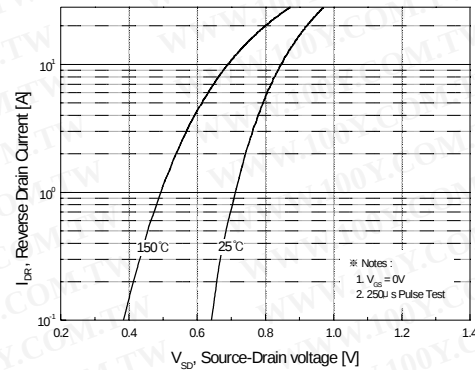


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

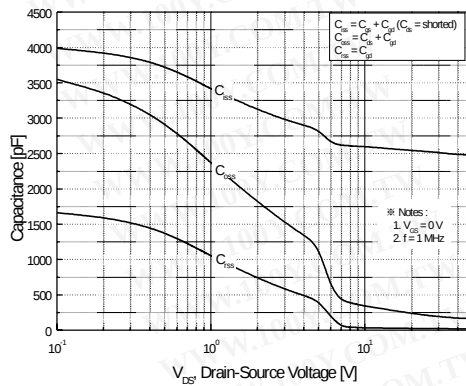


Figure 5. Capacitance Characteristics

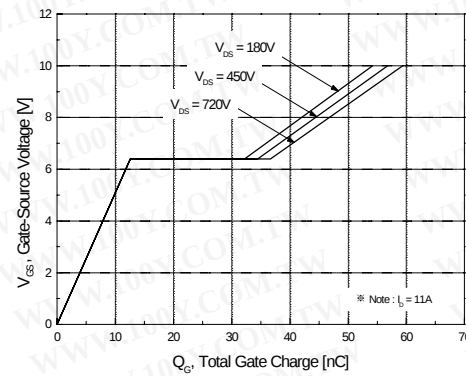


Figure 6. Gate Charge Characteristics

Typical Characteristics

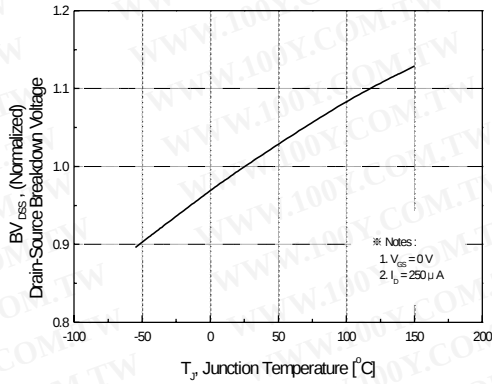


Figure 7. Breakdown Voltage Variation vs Temperature

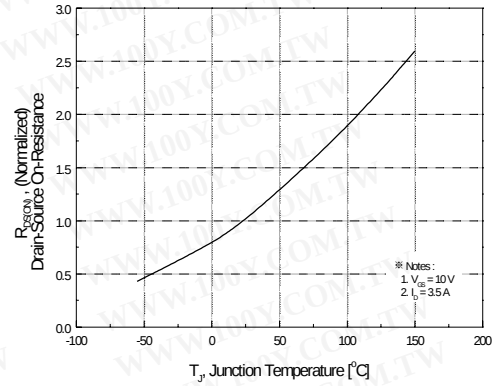


Figure 8. On-Resistance Variation vs Temperature

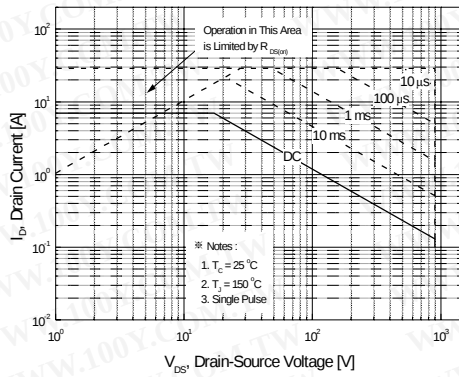


Figure 9. Maximum Safe Operating Area

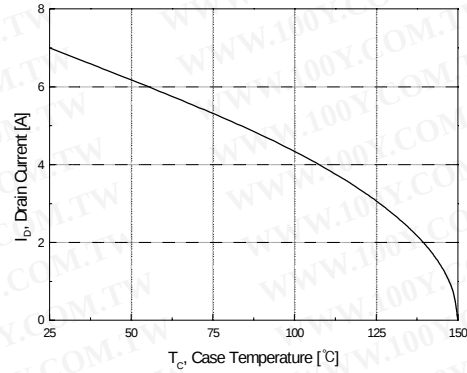


Figure 10. Maximum Drain Current vs Case Temperature

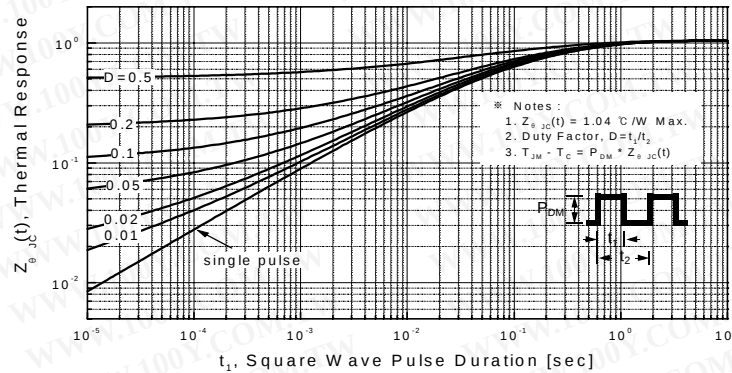
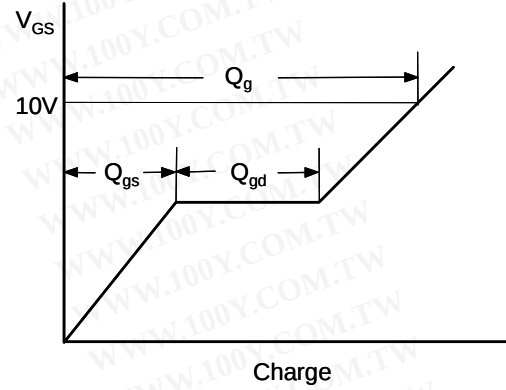
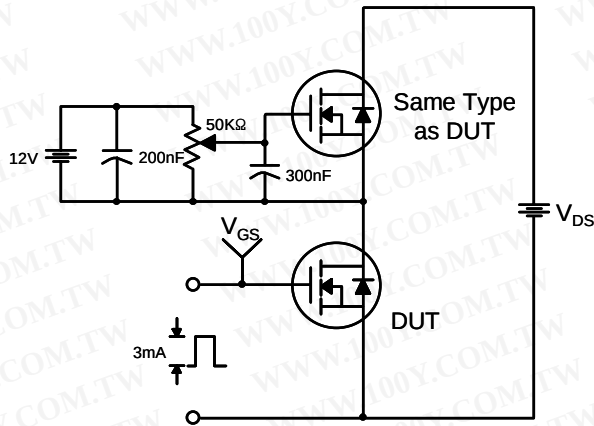
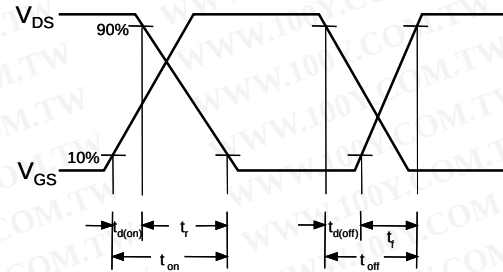
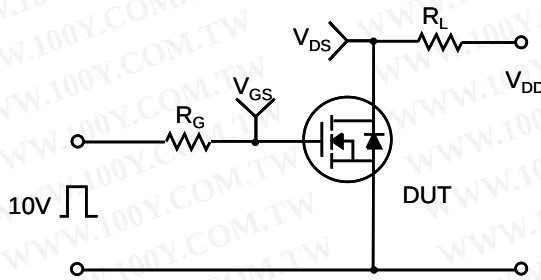


Figure 11. Transient Thermal Response Curve

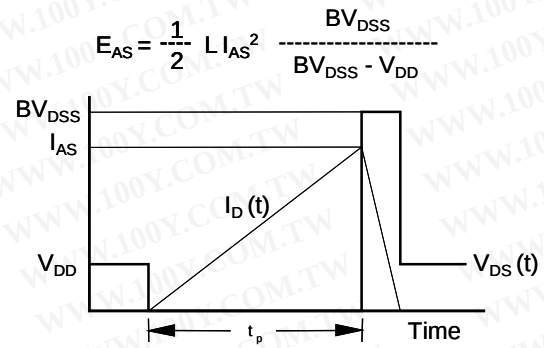
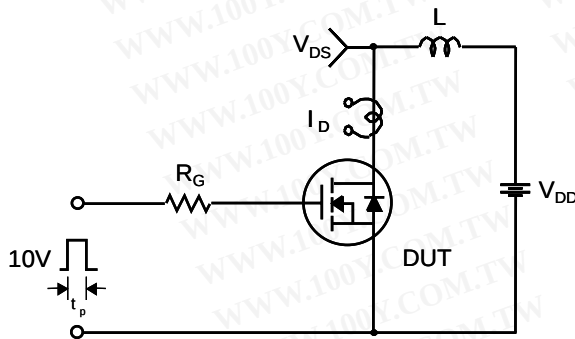
Gate Charge Test Circuit & Waveform

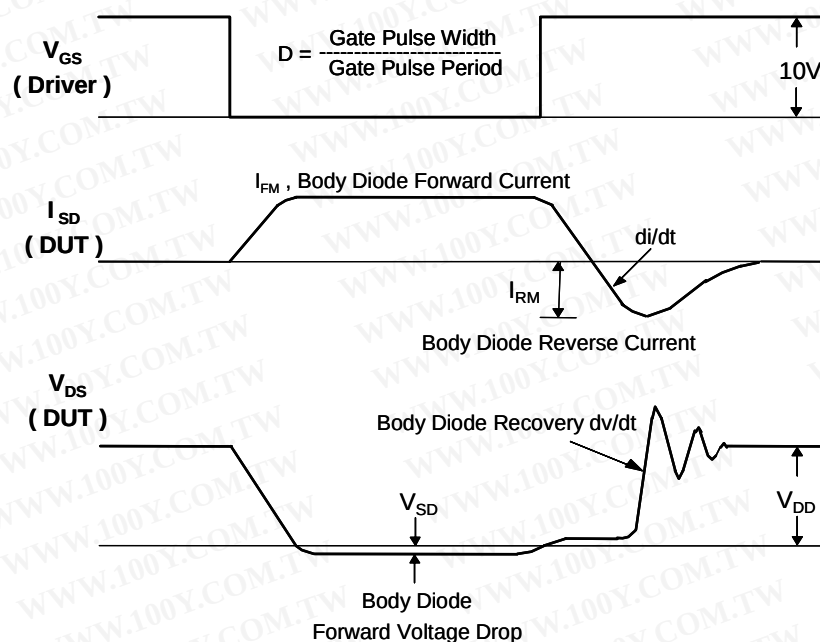
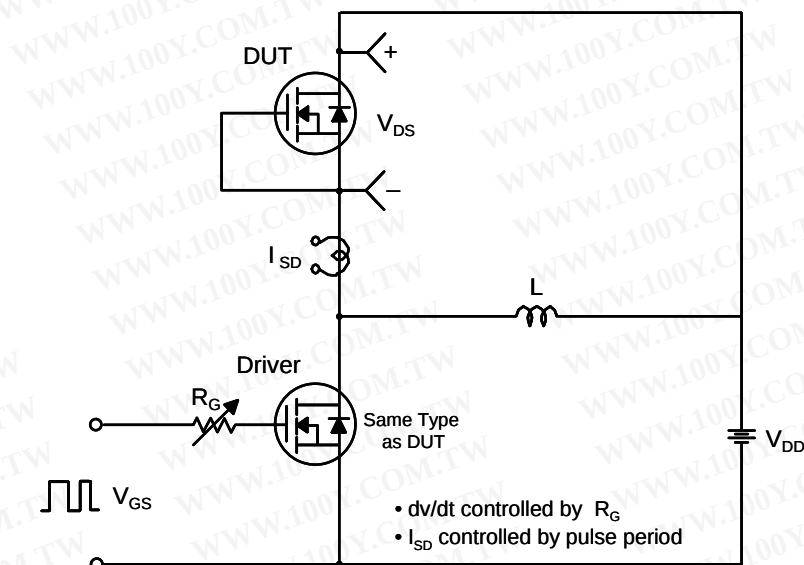


Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

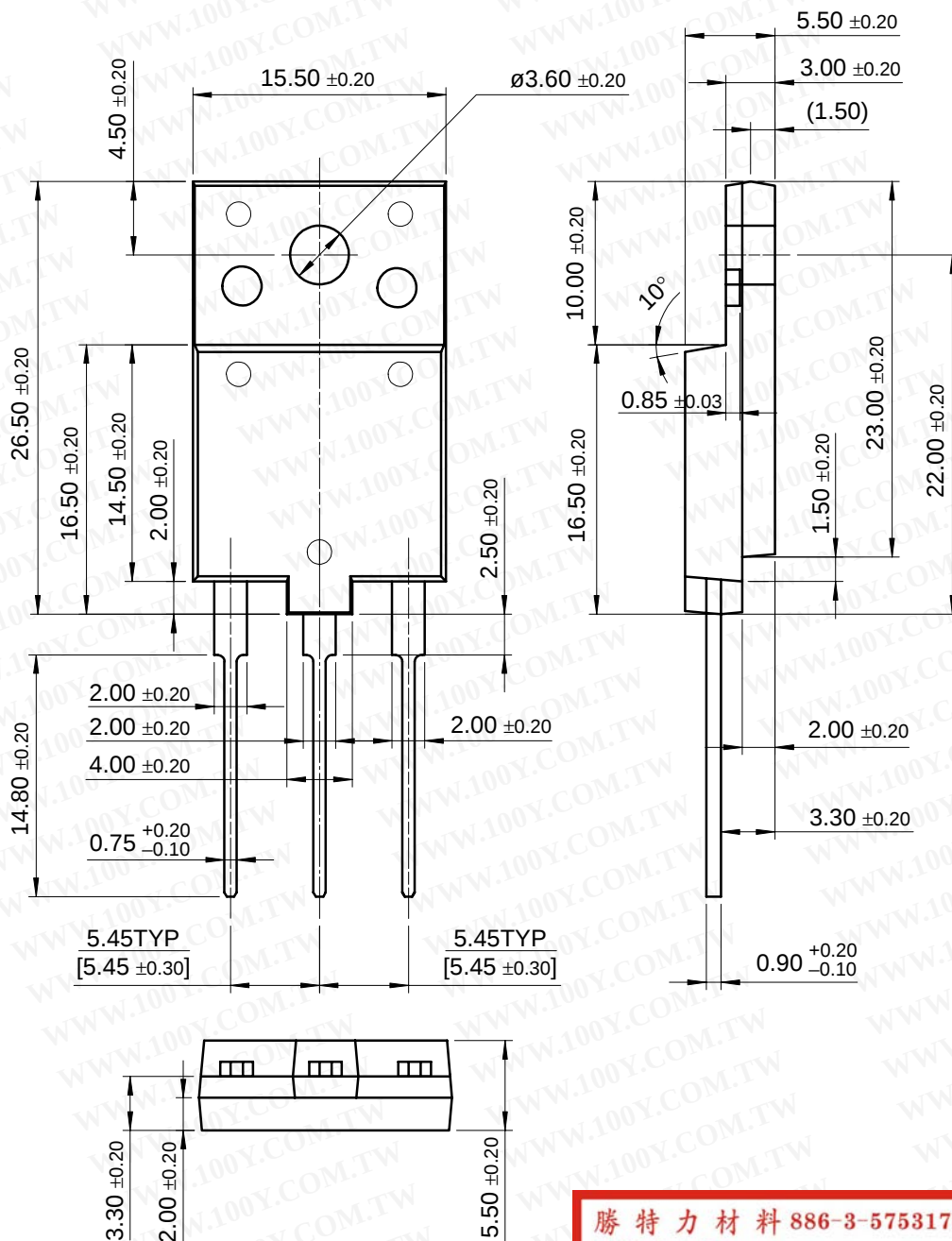


Peak Diode Recovery dv/dt Test Circuit & Waveforms

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